Infrared Emitting Diodes(GaAs)

KODENSHI

EL - 6F11

The EL - 6F11 is a high - power GaAs IRED mounted in a clear epoxy package. This IRED is both compact and easy to mount.

FEATURES

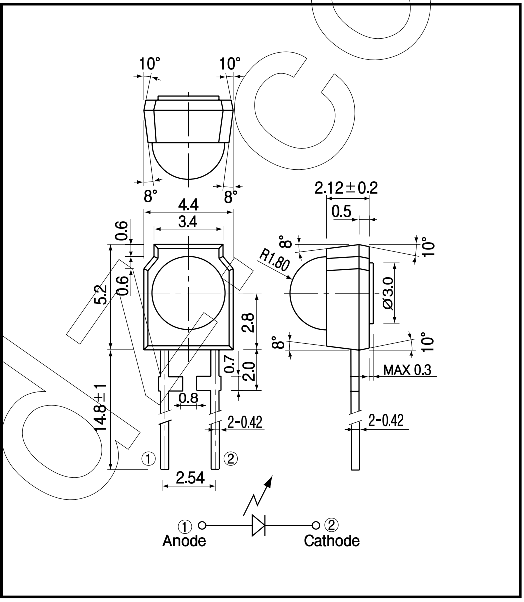
- Plastic mold package with a large caliber lens
- High output power

APPLICATIONS

- Optical switches

DIMENSIONS

(Unit : mm)



MAXIMUM RATINGS

(Ta=25℃)

Item	Symbol	Rating	Unit
Reverse voltage	V_R	4	V
Forward current	I_F	50	mA
Power dissipation	P_D	80	mW
Pulse forward current [*1]	I_{FP}	1	A
Operating temp.	Topr.	−25 +85	℃
Storage temp.	Tstg.	−40 +85	℃
Soldering temp. [*2]	Tsol.	260	℃

*1. pulse width : tw ≦100 μsec.period : T=10msec.

*2. For MAX.5 seconds at the position of 2 mm from the package

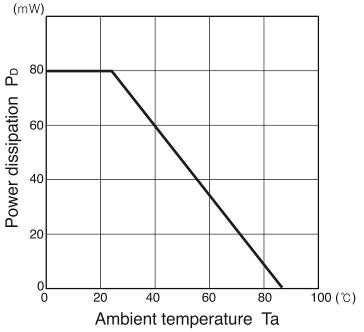
ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25℃)

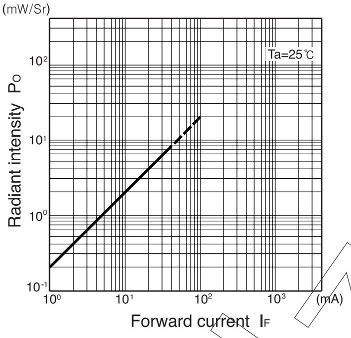
Item	Symbol	Conditions	Min.	Typ.	Max.	Unit.
Forward voltage	V_F	I_F=50mA		1.3	1.65	V
Reverse current	I_R	V_R=4V			10	μA
Peak emission wavelength	λp	I_F=20mA		940		nm
Spectral bandwidth	Δλ	I_F=20mA		50		nm
Radiant intensity [*3]	P_O	I_F=50mA	2.5	6.0		V
Half angle	Δθ	I_F=20mA		±25		deg.

*3. Measured by tester of KODENSHI CORP.

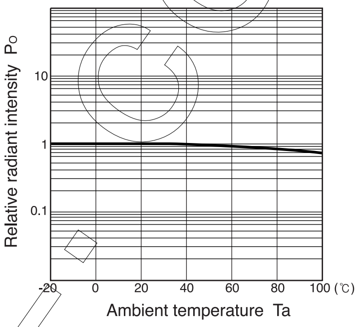
Power dissipation Vs. Ambient temperature



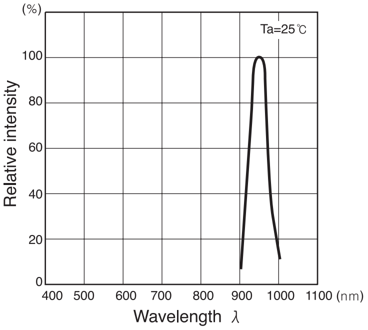
Radiant intensity Vs. Forward current



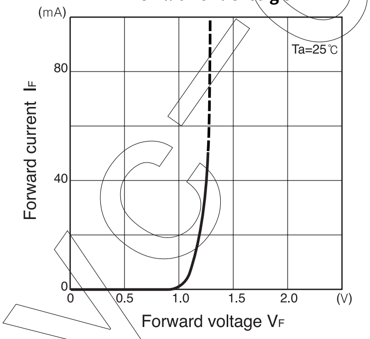
Relative radiant intensity Vs. Ambient temperature



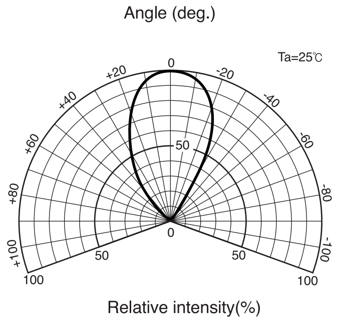
Relative intensity Vs. Wavelength



Forward current vs. Forward voltage



Radiant Pattern



Relative radiant intensity Vs. Distance